ESD and Surge Protection Diode

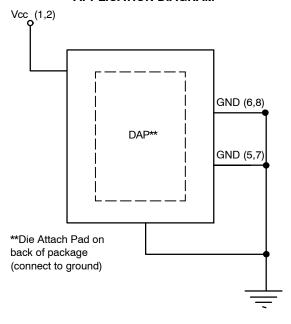
Low Clamping Voltage

NSPU5201, NSPU5221 Series

Features

- Unidirectional High Voltage ESD and Surge Protection
- Provides ESD Protection to IEC61000-4-2 Level 4: ±30 kV Contact Discharge
- Small Package: 1.8 mm x 2.0 mm
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

APPLICATION DIAGRAM





ON Semiconductor®

www.onsemi.com



UDFN6 CASE 517CS

BLOCK DIAGRAM



MARKING DIAGRAM



XX = Specific Device CodeM = Date Code= Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
NSPU5201MUTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NSPU5221MUTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

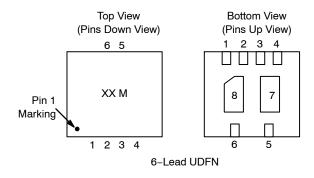
1

NSPU5201, NSPU5221 Series

Table 1. PIN DESCRIPTIONS

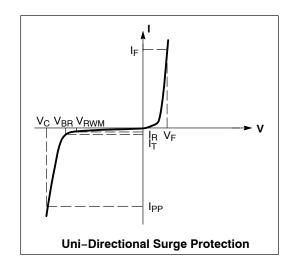
IUDI	Tubic 1.1 iii becomii 110110				
	6-Lead, UDFN8 Package				
Pin	Name	Description			
1	V _{CC}	Cathode			
2	V _{CC}	Cathode			
3	N/C	No Connect			
4	N/C	No Connect			
5	GND	Anode			
6	GND	Anode			
7	GND	Anode			
8	GND	Anode			

PACKAGE / PINOUT DIAGRAMS



ELECTRICAL CHARACTERISTICS

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
ΘV _{BR}	Maximum Temperature Coefficient of V _{BR}
I _F	Forward Current
V _F	Forward Voltage @ I _F



NSPU5201, NSPU5221 Series

SPECIFICATIONS

Table 2. MAXIMUM RATINGS

Parameter	Rating	Units
Operating Temperature Range	-55 to +125	°C
Storage Temperature Range	-65 to +150	°C

Stresses at or above those listed in Maximum Ratings table may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Also, due to variations in test equipment, stresses shown above are averages.

ELECTRICAL CHARACTERISTICS

				Breakdown Voltage			I PP (A) (8 x 20 μs)	V _C @ I _{PP} (8 x 20 μs)		
	Device	V _{RWM} (V)	I _R @ V _{RWM} (μΑ)	V _{BR} V		@ I _T (mA)		V _C (V)	I _{PP} (A)	
Device Name	Marking	Max	Max	Min	Nom	Max		Min	Max	
NSPU5201	AZ	20	1	21.7	22.7	23.7	1	140	31.5	110
NODUEOOA	40	20	1	0.4	05	00	,	100	33	100
NSPU5221	A2	22	2	24	25	26	1	120	35	120

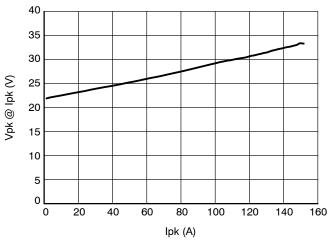
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (NSPU5221)

	Description	Min	Тур	Max	Unit
V _{CLAMP} Clamp Voltage	24 A IEC61000–4–5 Surge (8/20 $\mu s)$ from IO to GND, V_{IN} = 0 V before surge, 25°C		26.8	28.5	٧
	40 A IEC61000–4–5 Surge (8/20 $\mu s)$ from IO to GND, V_{IN} = 0 V before surge, 25°C		28.3	30	٧
	35 A IEC61000–4–5 Surge (8/20 $\mu s)$ from IO to GND, V_{IN} = V_{RWM} before surge, T_A = 125°C		29.4	31	٧

NSPU5201, NSPU5221 Series

TYPICAL CHARACTERISTICS



Vpk @ lpk (V) lpk (A)

Figure 1. NSPU5021 Positive Clamping Voltage vs. Peak Pulse Current ($t_p = 8/20 \mu s$)

Figure 2. NSPU5221 Positive Clamping Voltage vs. Peak Pulse Current (t_p = 8/20 μ s)

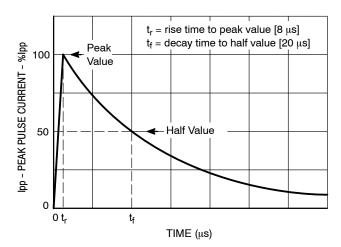
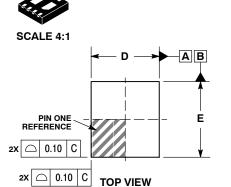
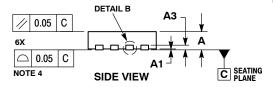


Figure 3. IEC61000-4-5 8/20 μs Pulse Waveform

DATE 30 APR 2013





DETAIL A

e1/2

2X D2 -

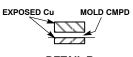
0.10 C

△ 0.10 C

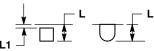
e1

BOTTOM VIEW

UDFN6, 1.8x2, 0.4P CASE 517CS **ISSUE 0**

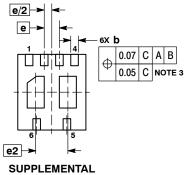


DETAIL B ALTERNATE CONSTRUCTION



ALTERNATE CONSTRUCTIONS





BOTTOM VIEW

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- 714.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSION 6 APPLIES TO PLATED TERMINALS
 AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.
 COPLANARITY APPLIES TO THE EXPOSED PAD
- AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.55		
A1	0.00	0.05		
A3	0.12	REF		
b	0.15 0.25			
D	1.80 BSC			
D2	0.35 0.55			
E	2.00 BSC			
E2	0.74 0.94			
е	0.40	BSC		
e1	0.80 BSC			
e2	0.95 BSC			
L	0.20 0.40			
L1	0.15			

GENERIC MARKING DIAGRAM*

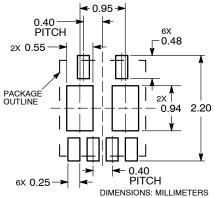


XX = Specific Device Code

= Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ", may or may not be present.

RECOMMENDED MOUNTING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	UDFN6 1.8X2, 0.4P		PAGE 1 OF 1			

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